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TITLE: Dielectric material for increasing
capacitance of capacitor of semiconductor device -
comprises mixed strontium barium titanate and has
high dielectric constant at room temp.

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PATENT-ASSIGNEE: SAMSUNG ELECTRONICS CO[SMSU]

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PATENT-FAMILY:

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KR 9206732 B		August 17, 1992	N/A
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APPLICATION-DATA:

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ABSTRACTED-PUB-NO: KR 9206732B

BASIC-ABSTRACT:

The dielectric substance for semiconductor device has compsn. of formula $\text{Sr}(1-x)\text{Ba}(x)\text{TiO}_3$ (where $x = 0$ to 0.3). The dielectric substance can undergo phase transition without any change in crystal structure at a temp. lower than room temp. and has high dielectric constant at room temp.

The stoichiometric
ratio of the dielectric substance compsn. is easily
adjusted since the elements
Sr, Ba and Ti are not vapourised. The dielectric substance
is used to increase
the capacitance of capacitor of semiconductor device.

DERWENT-CLASS: L03 U11 V01 X12

CPI-CODES: L03-B03E;

EPI-CODES: U11-A08A2; V01-B03A1; X12-E01A;